LDMOS 3-stage integrated Doherty MMIC

Rev. 1 — 14 November 2022

1. Product profile

1.1 General description

The B11G3338N81D is a dual section 3-stage fully integrated Doherty MMIC solution using Ampleon's state of the art LDMOS technology. The carrier and peaking device, input splitter, output combiner and pre-match are integrated in each section. This multiband device is perfectly suited as general purpose driver in the frequency range 3300 MHz to 3800 MHz. Available in PQFN outline.

Table 1. Application performance

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$; $I_{Dq} = 220 \ mA$ (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \ V$. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB measured in an Ampleon f = 3600 MHz combined integrated Doherty application circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	ησ
	(MHz)	(V)	(W)	(dB)	(%)
1-carrier LTE 20 MHz PAR = 7.6 dB	3600	28	5	33	21.5

1.2 Features and benefits

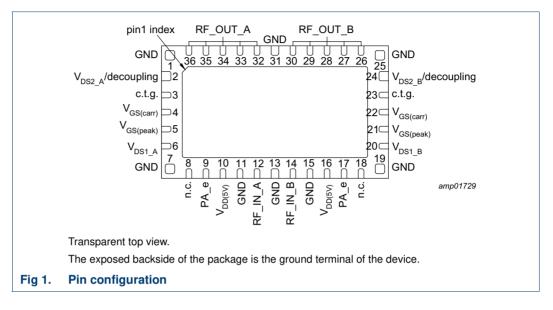
- Integrated input splitter
- Integrated output combiner
- **25** Ω output impedance thanks to integrated pre-match
- Designed for large RF and instantaneous bandwidth operation
- High linearity
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Integrated bias gate switch
- Source impedance 50 Ω; high power gain
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

- Macrocell base station driver
- Microcell base station
- 5G mMIMO
- W-CDMA/LTE
- Active antenna
- General purpose applications

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin desc	cription	
Symbol	Pin	Description
GND	1	ground
V _{DS2_A} /decoupling	2	drain-source voltage of final stages of section A
c.t.g.	3	connect to ground
V _{GS(carr)}	4	gate-source voltage of carrier [1]
V _{GS(peak)}	5	gate-source voltage of peaking [2]
V _{DS1_A}	6	drain-source voltage of driver stages of section A
GND	7	ground
n.c.	8	not connected
PA_e	9	PA enable trigger signal, 0 V to 5 V, $I_{Dq}\mbox{-bias}$ ON/OFF corresponds to logic HIGH/LOW $\ensuremath{\sc M}\mbox{-}$
V _{DD(5V)}	10	supply voltage (5 V) [4]
GND	11	ground
RF_IN_A	12	RF input of section A
GND	13	ground
RF_IN_B	14	RF input of section B
GND	15	ground
V _{DD(5V)}	16	supply voltage (5 V) [4]
PA_e	17	PA enable trigger signal, 0 V to 5 V, I _{Dq} -bias ON/OFF corresponds to logic HIGH/LOW [3]
n.c.	18	not connected
GND	19	ground

Table 2. Pin description

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Table 2.	Pin description	continued

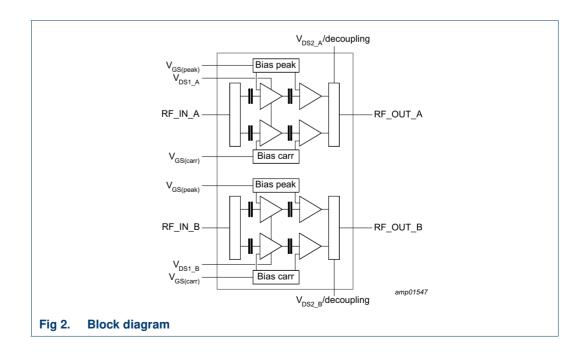
Symbol	Pin	Description		
V _{DS1_B}	20	drain-source voltage of driver stages of section B		
V _{GS(peak)}	21	gate-source voltage of peaking [2]		
V _{GS(carr)}	22	gate-source voltage of carrier [1]		
c.t.g.	23	connect to ground		
V _{DS2_B} /decoupling	24	drain-source voltage of final stages of section B		
GND	25	ground		
RF_OUT_B	26, 27, 28, 29, 30	RF output of section B		
GND	31	ground		
RF_OUT_A	32, 33, 34, 35, 36	RF output of section A		

- [1] Pins connected together.
- [2] Pins connected together.
- [3] Pins connected together.
- [4] Pins connected together.

3. Ordering information

Package name	Orderable part number	12NC	Packing description	Min. orderable quantity (pieces)
PQFN-12x7-36-1	B11G3338N81DX	9349 606 38525	TR13; 1500-fold; 24 mm; dry pack	1500
PQFN-12x7-36-1	B11G3338N81DYZ	9349 606 38535	TR7; 300-fold; 24 mm; dry pack	300

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-	65	V
V _{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	200	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics Measured for total device Image: Second Seco

Symbol	Parameter	Conditions		Value	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 90 °C			
		$P_L = 5 W$	[1]	1.7	K/W
		P _L = 10 W	[1]	1.4	K/W

[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

7. Characteristics

Table 6. DC characteristics

 $T_{case} = 25 \ ^{\circ}C; V_{DD(5V)} = 5 \ V; V_{on(PA \ e)} = 5 \ V.$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Carrier						
V _{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; \text{ I}_{D} = 210 \text{ mA}$	1.6	2.1	2.7	V
I _{GSS}	gate leakage current	$V_{GS} = 2 V; V_{DS} = 0 V$	-	-	140	nA
Peaking						
I _{GSS}	gate leakage current	$V_{GS} = 2 V; V_{DS} = 0 V$	-	-	140	nA
Final sta	ges					
I _{DSS}	drain leakage current	$V_{GS} = 0 V; V_{DS} = 28 V$	-	-	1.4	μA
Driver stages						
I _{DSS}	drain leakage current	$V_{GS} = 0 V; V_{DS} = 28 V$	-	-	1.4	μA

Table 7. RF characteristics

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 210 \ mA$ (carrier); $f = 3550 \ MHz$; $V_{DD(5V)} = 4.8 \ V$; $V_{on(PA_e)} = 5 \ V$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \ V$; $P_{L(AV)} = 5 \ W$; unless otherwise specified, measured in an Ampleon combined production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Test sigr	nal: pulsed CW [1]					
G _p	power gain	P _L = 5 W (37 dBm)	31	34	38	dB
η _D	drain efficiency	P _L = 5 W (37 dBm)	18	25	-	%
		$P_L = P_{L(3dB)}$	30	40	-	%
RL _{in}	input return loss		-	-15	-10	dB
P _{L(3dB)}	output power at 3 dB gain compression		48	49	-	dBm

[1] Pulsed CW power sweep measurement ($\delta = 10 \%$, t_p = 100 µs).

8. Application information

8.1 Typical performance

Table 8. Typical performance

 $T_{case} = 25 \text{ °C}; V_{DS} = 28 \text{ V}; I_{Dq} = 220 \text{ mA} (carrier and peaking); V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \text{ V}; V_{DD(5V)} = 5 \text{ V};$ $V_{on(PA_e)} = 5 \text{ V}.$ Test signal: 1-carrier W-CDMA; PAR = 9.9 dB; unless otherwise specified, measured in an Ampleon 3300 MHz to 3800 MHz frequency band combined application circuit.

Symbol	Parameter	Conditions	М	in Typ	Max	Unit
P _{L(1dB)}	output power at 1 dB gain compression	f = 3600 MHz	1] _	48.7	-	dBm
$\phi_{s21}/\phi_{s21}(norm)$	normalized phase response	at 1 dB compression point; f = 3600 MHz	2] _	-16	-	0
η _D	drain efficiency	12.2 dB OBO (P _{L(AV)} = 37 dBm); f = 3600 MHz	-	22	-	%
G _p	power gain	P _{L(AV)} = 37 dBm; f = 3600 MHz	-	33	-	dB
B _{video}	video bandwidth	$P_{L(AV)} = 37 \text{ dBm set to obtain}$ IMD3 = -45 dBc; f = 3600 MHz	-	350	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 37 dBm; f = 3300 MHz to 3800 MHz	-	0.6	-	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 37 dBm; f = 3600 MHz	-	-39	-	dBc
$\Delta G / \Delta T$	gain variation with temperature	f = 3600 MHz	-	0.068	-	dB/°C
К	Rollett stability factor	T _{case} = -40 °C to +125 °C; f = 0.1 GHz to 8 GHz	3] -	>1	-	
Bias gate swi	tch		1			
t _r	rise time	$ Z_S = 500 \ \Omega \ (max); T_{case} = -40 \ ^\circ C \ to \\ +120 \ ^\circ C; \ V_{on(PA_e)} \ge 4.8 \ V $	<u>[4]</u> _	200	-	ns
t _f	fall time	$ \begin{array}{l} T_{case} = -40 \ ^{\circ}C \ to \ +120 \ ^{\circ}C; \\ V_{off(PA_e)} \leq 1 \ V \end{array} $	<u>5]</u> _	80	-	ns

[1] Pulsed CW power sweep measurement ($\delta = 10$ %, $t_p = 100 \ \mu$ s).

[2] 25 ms CW power sweep measurement.

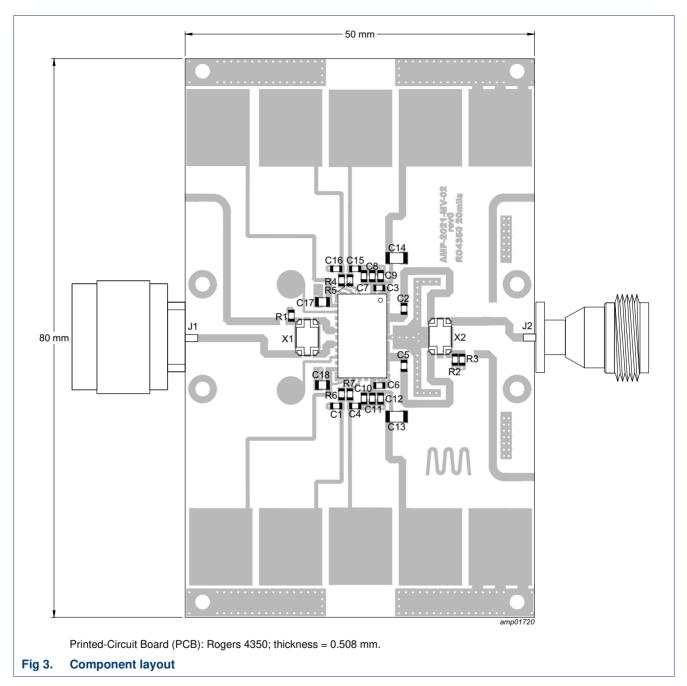
[3] With input VSWR better than 30 : 1 and output VSWR better than 80 : 1.

[4] RF output rise time 10 % to 90 % RF power.

[5] RF output fall time 90 % to 10 % RF power.

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8.2 PCB layout and electrical schematic

Table 9.Demo test circuit list of componentsSee Figure 3 for component layout.

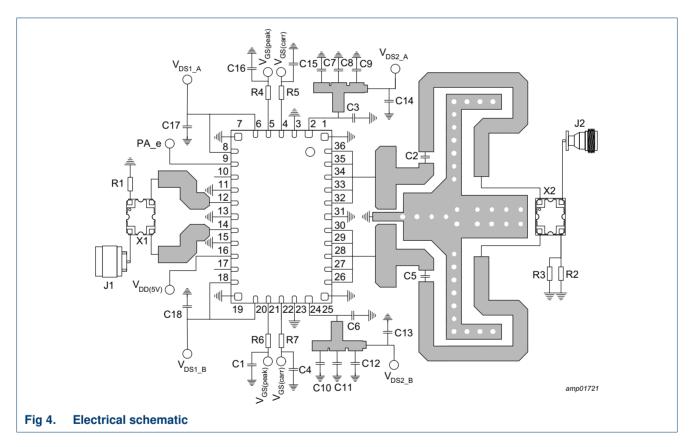
Component	Description	Value	Remarks
C1, C4, C15, C16	multilayer ceramic chip capacitor	1 μF, 50 V	Murata: C1608X5R1H105K080AB
C2, C5	multilayer ceramic chip capacitor	1.6 pF, ± 0.1 %	Murata: GQM1875C2E1R6BB12
C3, C6	multilayer ceramic chip capacitor	4.3 pF, ± 0.1 %	Murata: GQM1875C2E4R3BB12

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Table 9. Demo test circuit list of components ...continued

See <u>Figure 3</u> for component layout.

Component	Description	Value	Remarks
C7, C8, C9, C10, C11, C12	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: 06035C104KAT2A
C13, C14, C17, C18	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: GRM21BR6YA106KE43
R1	resistor	49.9 Ω , ± 1 %, 100 mW	Multicomp Pro: MCWF06R49R9BTL
R2, R3	resistor	100 Ω,\pm 1 %, 200 mW	Multicomp Pro: MP001293
R4, R5, R6, R7	resistor	1 k Ω , \pm 1 %, 100 mW	Multicomp Pro: MCSR06X1001FTL
X1, X2	hybrid coupler	3.3 GHz – 3.8 GHz, 25 W	Anaren: X3C35F1-03S
J1	N Coaxial panel connector male		Radiall: R161.438.200
J2	N Coaxial panel connector female		Huber & Suhner: 23_N-50-0-16/133_NE



8.3 Recommendations

- RC circuit at gate bias must be implemented to insure improved linearity and stability of the circuit. The implementation has to be symmetrical between both amplifier sections Pin 5/21 and Pin 4/22.
- In TDD mode controlled by an external bias switch, the outputs of the switches must be connected on both amplifier sections. As shown in Fig.4, gate bias supply must be connected before RC circuit of Pin 5/21 and Pin 4/22 respectively by default.

8.4 Ruggedness in a Doherty operation

8.4.1 Output mismatch ruggedness

The B11G3338N81D is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 32$ V; $I_{Dq} = 105$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V; $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V; P_i corresponding to $P_{L(3dB)} - 9$ dB under $Z_S = 50 \Omega$ load; f = 3800 MHz (1-carrier W-CDMA); $T_{case} = 25$ °C; per section.

8.4.2 Wideband noise ruggedness

The B11G3338N81D is capable of withstanding an AWGN (Additive White Gaussian Noise) with 11.2 dB PAR, OBW (Occupied BandWidth) of 900 MHz, under the following conditions: $V_{DS} = 32$ V; $I_{Dq} = 105$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65$ V; $V_{DD(5V)} = 5$ V; $V_{on(PA_e)} = 5$ V; 3 dB P_i overdrive from $P_{L(AV)} = 34$ dBm (corresponding to $P_{L(3dB)} - 12$ dB); f = 3550 MHz as central frequency; $T_{case} = 25$ °C; per section.

8.5 Impedance information

Table 10. Typical impedance for optimum Doherty operation

Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25 \text{ °C}$; $V_{DS} = 28 \text{ V}$; $I_{Dq} = 105 \text{ mA} \text{ (carrier)}$; $V_{DD(5V)} = 5 \text{ V}$; $V_{on(PA_e)} = 5 \text{ V}$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.65 \text{ V}$; $t_p = 100 \ \mu\text{s}$; $\delta = 10 \ \%$.

	tuned for optimu	tuned for optimum Doherty operation			
f	Z _L [1]	P _{L(1dB)}	G _{p(max)}	໗ <mark>add ^[2]</mark>	໗ _{add} [3]
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)
3300	21.5 – j19.3	46.34	34.9	44.1	22.1
3400	21.4 – j17.2	46.30	35.3	44.3	22.7
3500	22.3 – j16.4	46.50	35.7	45.2	22.9
3600	23.9 – j13.4	46.30	35.7	44.3	23.7
3700	24.0 - j13.4	46.30	35.3	44.6	23.3
3800	22.7 – j11.4	46.20	35.0	44.1	23.4

[1] Reference package plane.

[2] At P_{L(1dB)}.

[3] At 34 dBm.

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9. Package outline

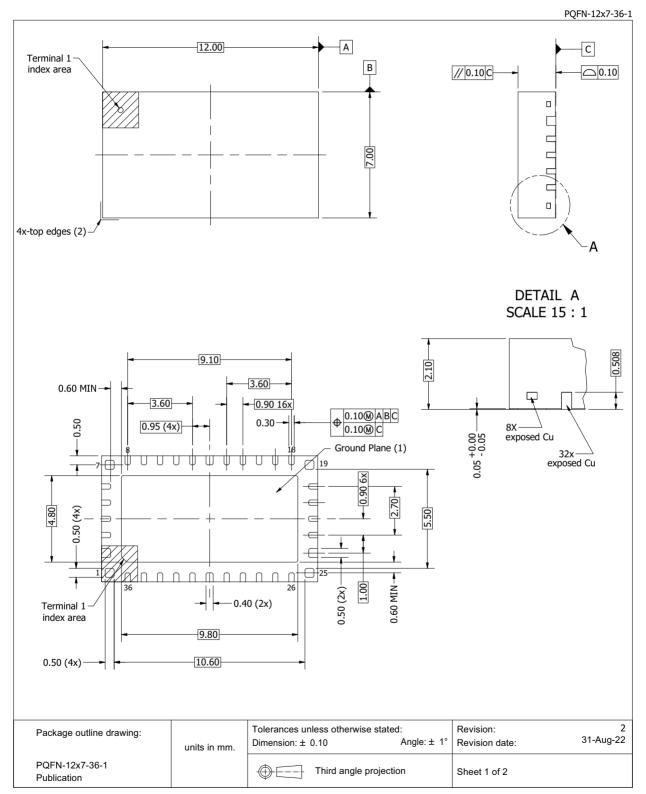


Fig 5. Package outline PQFN-12x7-36-1 (sheet 1 of 2)

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PQFN-12x7-36-1

			Drawing Notes	
Items			Description	
(1)			ttom View) are plated with matte Sn.	
(2)	Plastic protrusions of 0.07	75 mm. max. per si	ide are not included.	
				Devision
Packa	age outline drawing:		Tolerances unless otherwise stated:	Revision: 31-AL
Packa	age outline drawing:	units in mm.	Tolerances unless otherwise stated: Dimension: ± 0.10 Angle: ± 1°	Revision: Revision date: 31-Au
	age outline drawing:	units in mm.		

Fig 6. Package outline PQFN-12x7-36-1 (sheet 2 of 2)

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C1 🗓
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C 🗳

[1] CDM classification C1 is granted to any part that passes after exposure to an ESD pulse of 250 V.

[2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations			
Acronym	Description		
5G	Fifth Generation		
CW	Continuous Wave		
ESD	ElectroStatic Discharge		
LDMOS	Laterally Diffused Metal Oxide Semiconductor		
LTE	Long Term Evolution		
mMIMO	massive Multiple Input Multiple Output		
MMIC	Monolithic Microwave Integrated Circuit		
MTF	Median Time to Failure		
OBO	Output Back Off		
PA	Power Amplifier		
PAR	Peak-to-Average power Ratio		
RC	resistor-capacitor		
RoHS	Restriction of Hazardous Substances		
TDD	Time Division Duplex		
VSWR	Voltage Standing Wave Ratio		
W-CDMA	Wideband Code Division Multiple Access		

12. Revision history

Table 13.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
B11G3338N81D v.1	20221114	Product data sheet	-	

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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